

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re New Patent Application of)
Koichiro TANAKA)
Japanese Priority Application No. 2000-399462) Attn: Applications
Japanese Priority Date: December 27, 2000) Branch
For: LASER ANNEALING METHOD AND)
SEMICONDUCTOR DEVICE)
FABRICATING METHOD) Date: December 19, 2001

PRELIMINARY AMENDMENT

Honorable Commissioner for Patents and Trademarks
Washington, D.C. 20231

Sir:

Please preliminarily amend the subject application as follows:

IN THE SPECIFICATION:

Please amend the specification as follows: Please note that specification is are presented below in its amended form. It is further presented as an Attachment to the Amendment whereby the amendments to the specification are outlined using the conventional method of bracketing and underlining.

Please amend the specification at page 13, paragraph 9 as follows:

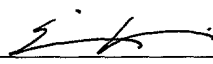
Figs. 22A to 22D are views showing different examples of the semiconductor device; and

REMARKS

The specification has been amended to correct the description of Figure 22 in the Brief Description of the Drawings.

Examination on the merits is requested.

Respectfully submitted,



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VERSION WITH MARKINGS TO SHOW CHANGES MADE

Figs. 22A to [22F] 22D are views showing different examples of the semiconductor device; and

FIG. 22A